

# MA4X862

Silicon epitaxial planar type

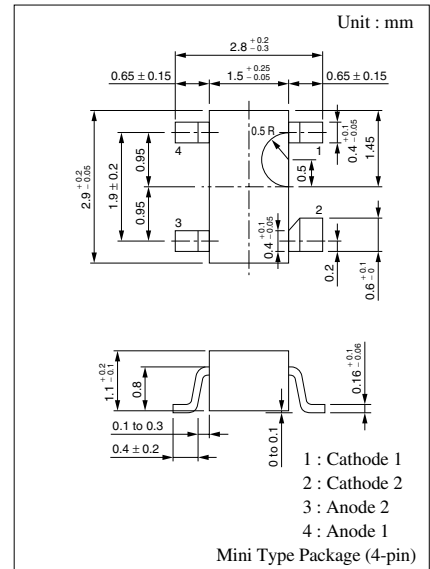
For band switching

### ■ Features

- Two electrically isolated elements incorporated
- Small diode capacitance  $C_D$
- Low forward dynamic resistance  $r_f$
- Optimum for a band switching of a tuner

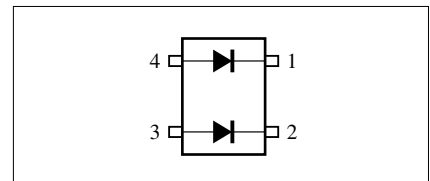
### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

| Parameter                     | Symbol    | Rating      | Unit             |
|-------------------------------|-----------|-------------|------------------|
| Reverse voltage (DC)          | $V_R$     | 35          | V                |
| Forward current (DC)          | Single    | $I_F$       | 100 mA           |
|                               | Double    |             | 75 mA/Unit       |
| Operating ambient temperature | $T_{opr}$ | -25 to +85  | $^\circ\text{C}$ |
| Storage temperature           | $T_{stg}$ | -55 to +100 | $^\circ\text{C}$ |



Marking Symbol: M11

Internal Connection



### ■ Electrical Characteristics $T_a = 25^\circ\text{C}$

| Parameter                  | Symbol        | Conditions                              | Min | Typ | Max  | Unit     |
|----------------------------|---------------|---|-----|-----|------|----------|
| Reverse current (DC)       | $I_R$         | $V_R = 33\text{ V}$                     |     |     | 100  | nA       |
| Forward voltage (DC)       | $V_F$         | $I_F = 100\text{ mA}$                   |     |     | 1.0  | V        |
| Diode capacitance          | $C_D$         | $V_R = 6\text{ V}, f = 1\text{ MHz}$    |     |     | 1.2  | pF       |
| Forward dynamic resistance | $r_{f1}^{*1}$ | $I_F = 2\text{ mA}, f = 100\text{ MHz}$ |     |     | 0.65 | $\Omega$ |
|                            | $r_{f2}^{*2}$ |   |     |     | 0.98 | $\Omega$ |

Note) 1. Rated input/output frequency: 100 MHz

2. \*1 :  $r_f$  measuring instrument: Nihon Koshuha Model TDC-121A

\*2 :  $r_f$  measuring instrument: YHP 4191A RF IMPEDANCE ANALYZER

